

# XN0421N (XN421N)

## Silicon NPN epitaxial planar type

For switching/digital circuits

### ■ Features

- Two elements incorporated into one package  
(Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

### ■ Basic Part Number

- UNR221N (UN221N) × 2

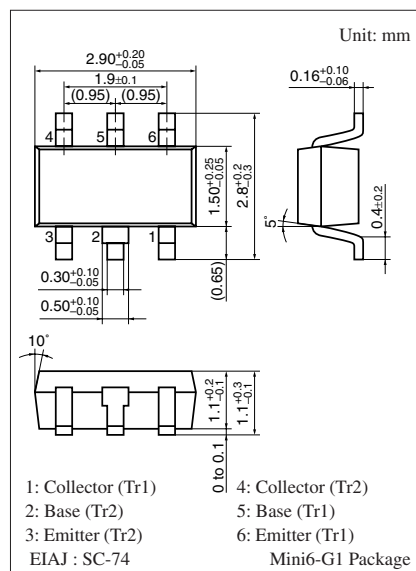
### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter                             | Symbol    | Rating      | Unit             |
|---------------------------------------|-----------|-------------|------------------|
| Collector-base voltage (Emitter open) | $V_{CBO}$ | 50          | V                |
| Collector-emitter voltage (Base open) | $V_{CEO}$ | 50          | V                |
| Collector current                     | $I_C$     | 100         | mA               |
| Total power dissipation               | $P_T$     | 300         | mW               |
| Junction temperature                  | $T_j$     | 150         | $^\circ\text{C}$ |
| Storage temperature                   | $T_{stg}$ | -55 to +150 | $^\circ\text{C}$ |

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

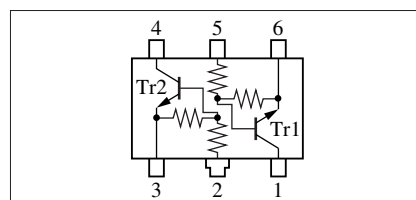
| Parameter                                    | Symbol        | Conditions                                                                 | Min  | Typ | Max  | Unit             |
|----------------------------------------------|---------------|----------------------------------------------------------------------------|------|-----|------|------------------|
| Collector-base voltage (Emitter open)        | $V_{CBO}$     | $I_C = 10\ \mu\text{A}$ , $I_E = 0$                                        | 50   |     |      | V                |
| Collector-emitter voltage (Base open)        | $V_{CEO}$     | $I_C = 2\ \text{mA}$ , $I_B = 0$                                           | 50   |     |      | V                |
| Collector-base cutoff current (Emitter open) | $I_{CBO}$     | $V_{CB} = 50\ \text{V}$ , $I_E = 0$                                        |      |     | 0.1  | $\mu\text{A}$    |
| Collector-emitter cutoff current (Base open) | $I_{CEO}$     | $V_{CE} = 50\ \text{V}$ , $I_B = 0$                                        |      |     | 0.5  | $\mu\text{A}$    |
| Emitter-base cutoff current (Collector open) | $I_{EBO}$     | $V_{EB} = 6\ \text{V}$ , $I_C = 0$                                         |      |     | 0.2  | mA               |
| Forward current transfer ratio               | $h_{FE}$      | $V_{CE} = 10\ \text{V}$ , $I_C = 5\ \text{mA}$                             | 80   |     | 400  | —                |
| Collector-emitter saturation voltage         | $V_{CE(sat)}$ | $I_C = 10\ \text{mA}$ , $I_B = 0.3\ \text{mA}$                             |      |     | 0.25 | V                |
| Output voltage high-level                    | $V_{OH}$      | $V_{CC} = 5\ \text{V}$ , $V_B = 0.5\ \text{V}$ , $R_L = 1\ \text{k}\Omega$ | 4.9  |     |      | V                |
| Output voltage low-level                     | $V_{OL}$      | $V_{CC} = 5\ \text{V}$ , $V_B = 2.5\ \text{V}$ , $R_L = 1\ \text{k}\Omega$ |      |     | 0.2  | V                |
| Input resistance                             | $R_i$         |                                                                            | -30% | 4.7 | +30% | $\text{k}\Omega$ |
| Resistance ratio                             | $R_1 / R_2$   |                                                                            |      | 0.1 |      | —                |
| Transition frequency                         | $f_T$         | $V_{CB} = 10\ \text{V}$ , $I_E = -2\ \text{mA}$ , $f = 200\ \text{MHz}$    |      | 150 |      | MHz              |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

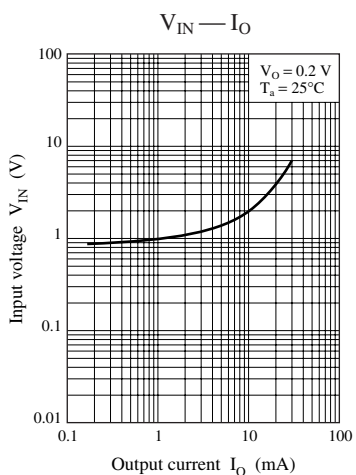
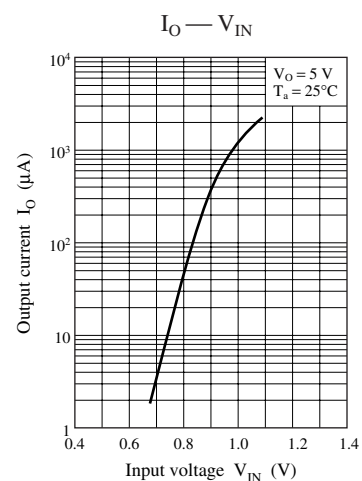
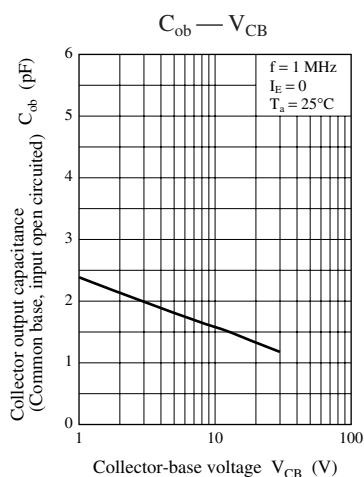
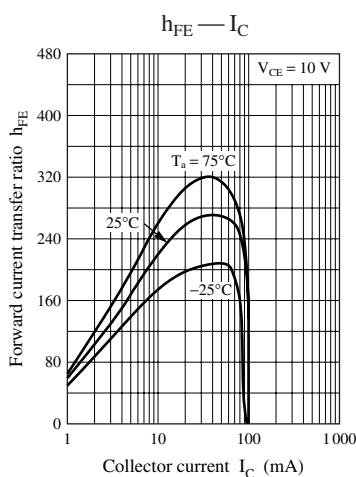
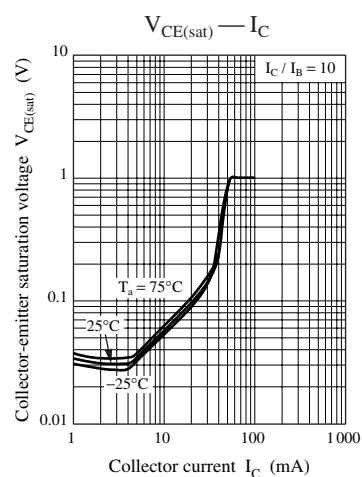
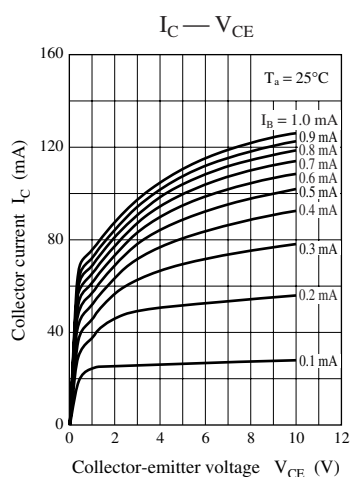
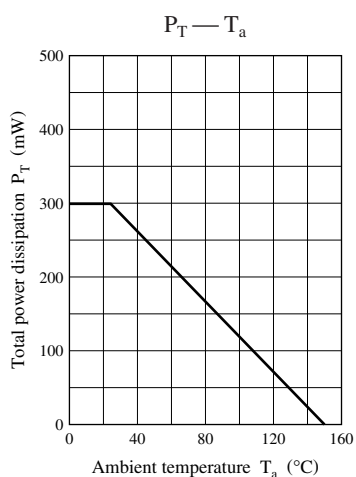


Marking Symbol: FK

Internal Connection



Note) The part number in the parenthesis shows conventional part number.



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